

BU208A BU508A/BU508AFI

HIGH VOLTAGE FAST-SWITCHING NPN POWER TRANSISTORS

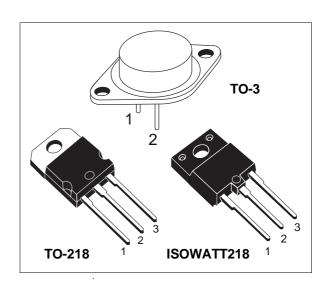
- STMicroelectronics PREFERRED SALESTYPES
- HIGH VOLTAGE CAPABILITY (> 1500 V)
- FULLY INSULATED PACKAGE (U.L. COMPLIANT) FOR EASY MOUNTING

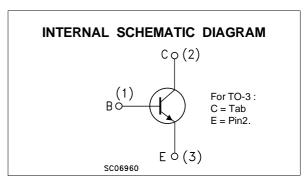
APPLICATIONS:

 HORIZONTAL DEFLECTION FOR COLOUR TV

DESCRIPTION

The BU208A, BU508A and BU508AFI are manufactured using Multiepitaxial Mesa technology for cost-effective high performance and use a Hollow Emitter structure to enhance switching speeds.





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter		Value			
V _{CES}	Collector-Emitter Voltage (V _{BE} = 0)		1500			
V _{CEO}	Collector-Emitter Voltage (I _B = 0)		700		٧	
V_{EBO}	Emitter-Base Voltage (I _C = 0)		10			
Ic	Collector Current	8			Α	
I _{CM}	Collector Peak Current (t _p < 5 ms)	15			Α	
		BU208A	BU508A	BU508AFI		
		TO - 3	TO - 218	ISOWATT218		
P _{tot}	Total Dissipation at T _c = 25 °C	150	125	50	W	
V _{isol}	Insulation Withstand Voltage (RMS) from All Three Leads to Exernal Heatsink			2500	V	
T _{stg}	Storage Temperature	-65 to 175	-65 to 150	-65 to 150	°C	
Tj	Max. Operating Junction Temperature	175	150	150	°C	

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BU208A / BU508A / BU508AFI

THERMAL DATA

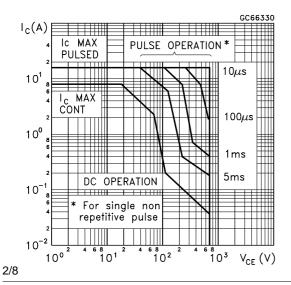
			TO-3	TO-218	ISOWATT218	
R _{thj-case}	Thermal Resistance Junction-case	Max	1	1	2.5	°C/W

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

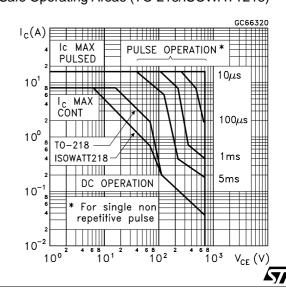
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
I _{CES}	Collector Cut-off Current (V _{BE} = 0)	V _{CE} = 1500 V V _{CE} = 1500 V T _C = 125 °C			1 2	mA mA
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = 5 V			100	μΑ
V _{CEO(sus)} *	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = 100 mA	700			V
V_{EBO}	Emitter Base Voltage (I _C = 0)	I _E = 10 mA	10			V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	$I_C = 4.5 \text{ A}$ $I_B = 2 \text{ A}$			1	V
V _{BE(sat)} *	Base-Emitter Saturation Voltage	I _C = 4.5 A I _B = 2 A			1.3	V
t _s	INDUCTIVE LOAD Storage Time Fall Time	$I_{C} = 4.5 \text{ A}$ $h_{FE} = 2.5 \text{ V}_{CC} = 140 \text{ V}$ $L_{C} = 0.9 \text{ mH}$ $L_{B} = 3 \mu\text{H}$		7 550		μs ns
f⊤	Transition Frequency	I _C = 0.1 A V _{CE} = 5 V f = 5 MHz		7		MHz

^{*} Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

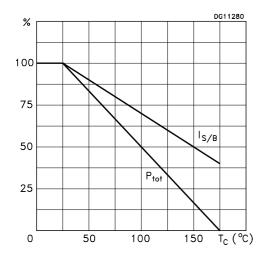
Safe Operating Area (TO-3)



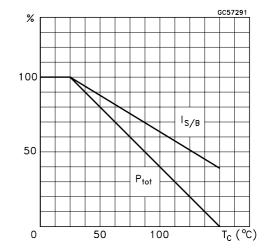
Safe Operating Areas (TO-218/ISOWATT218)



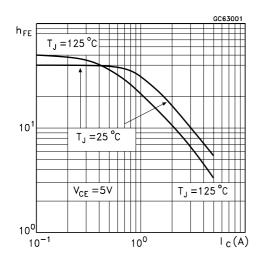
Derating Curves (TO-3)



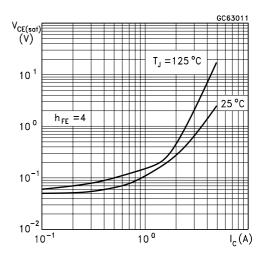
Derating Curves (TO-218/ISOWATT218)



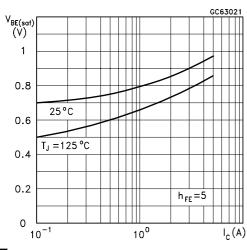
DC Current Gain



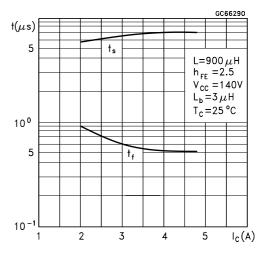
Collector Emitter Saturation Voltage



Base Emitter Saturation Voltage



Switching Time Inductive Load



Switching Time Inductive Load

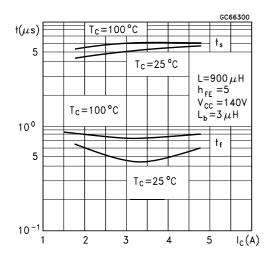
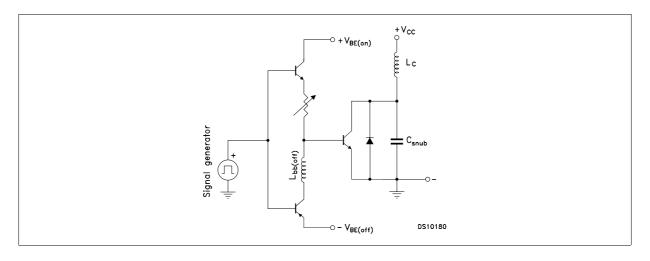
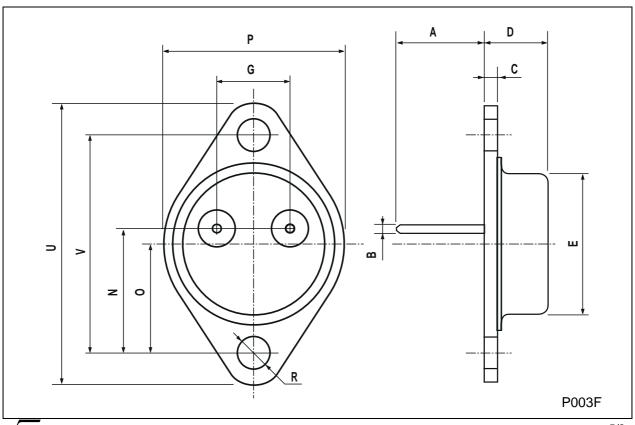


Figure 1: Inductive Load Switching Test Circuit.



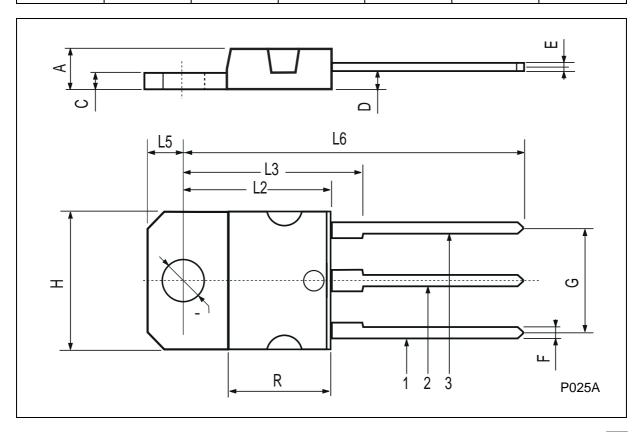
TO-3 MECHANICAL DATA

DIM.	mm			inch			
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А	11.00		13.10	0.433		0.516	
В	0.97		1.15	0.038		0.045	
С	1.50		1.65	0.059		0.065	
D	8.32		8.92	0.327		0.351	
E	19.00		20.00	0.748		0.787	
G	10.70		11.10	0.421		0.437	
N	16.50		17.20	0.649		0.677	
Р	25.00		26.00	0.984		1.023	
R	4.00		4.09	0.157		0.161	
U	38.50		39.30	1.515		1.547	
V	30.00		30.30	1.187		1.193	



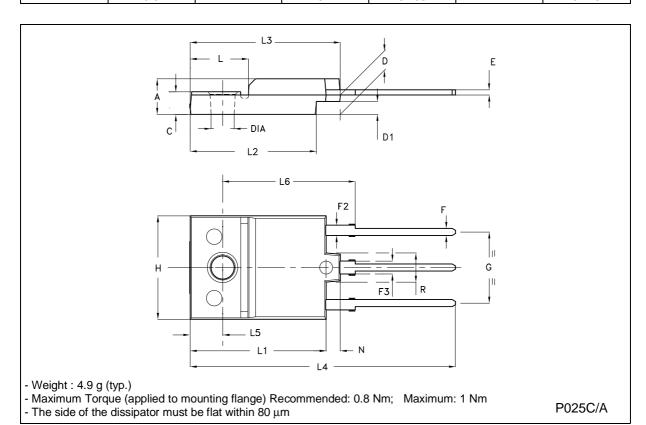
TO-218 (SOT-93) MECHANICAL DATA

DIM.	mm			inch			
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А	4.7		4.9	0.185		0.193	
С	1.17		1.37	0.046		0.054	
D		2.5			0.098		
Е	0.5		0.78	0.019		0.030	
F	1.1		1.3	0.043		0.051	
G	10.8		11.1	0.425		0.437	
Н	14.7		15.2	0.578		0.598	
L2	_		16.2	_		0.637	
L3		18			0.708		
L5	3.95		4.15	0.155		0.163	
L6		31			1.220		
R	_		12.2	-		0.480	
Ø	4		4.1	0.157		0.161	



ISOWATT218 MECHANICAL DATA

DIM		mm			inch	
DIM.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
Α	5.35		5.65	0.211		0.222
С	3.30		3.80	0.130		0.150
D	2.90		3.10	0.114		0.122
D1	1.88		2.08	0.074		0.082
Е	0.75		0.95	0.030		0.037
F	1.05		1.25	0.041		0.049
F2	1.50		1.70	0.059		0.067
F3	1.90		2.10	0.075		0.083
G	10.80		11.20	0.425		0.441
Н	15.80		16.20	0.622		0.638
L		9			0.354	
L1	20.80		21.20	0.819		0.835
L2	19.10		19.90	0.752		0.783
L3	22.80		23.60	0.898		0.929
L4	40.50		42.50	1.594		1.673
L5	4.85		5.25	0.191		0.207
L6	20.25		20.75	0.797		0.817
N	2.1		2.3	0.083		0.091
R		4.6			0.181	
DIA	3.5		3.7	0.138		0.146



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